# ASSP VOLTAGE DETECTOR

# **MB3761**

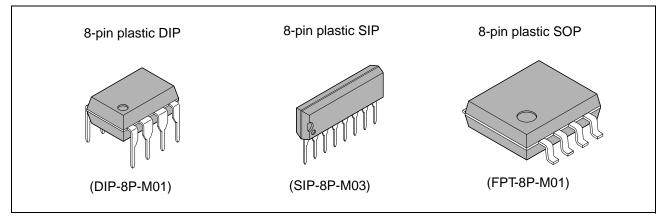
# DESCRIPTION

Designed for voltage detector applications, the Fujitsu MB3761 is a dual comparator with a built-in high precision reference voltage generator. Outputs are open-collector outputs and enable use of the OR-connection between both channels. Both channels have hysteresis control outputs. Because of a wide power supply voltage range and a low power supply current, the MB3761 is suitable for power supply monitors and battery backup systems.

# FEATURES

- Wide power supply voltage range: 2.5 V to 40 V
- Low power and small voltage dependency supply current: 250  $\mu\text{A}$  Typ
- Built-in stable low voltage generator: 1.20 V Typ
- Easy-to-add hysteresis characteristics.
- Package: 8-pin Plastic SIP Package (Suffix: -PS)
  - 8-pin Plastic DIP Package (Suffix: -P)
  - 8-pin Plastic SOP Package (Suffix: -PF)

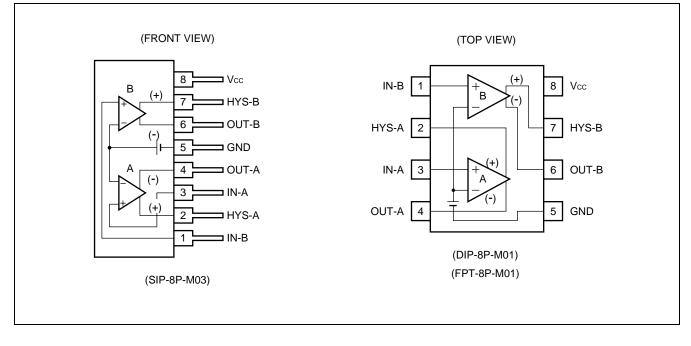
# PACKAGE



Note : This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.



# ■ PIN ASSIGNMENT



## ABSOLUTE MAXIMUM RATINGS

| Parameter            | Symbol | Rat   | Unit                            |      |
|----------------------|--------|-------|---------------------------------|------|
|                      |        | Min   | Max                             | Onit |
| Power Supply Voltage | Vcc    |       | 41                              | V    |
| Output Voltage       | Vo     |       | 41                              | V    |
| Output Current       | lo     |       | 50                              | mA   |
| Input Voltage        | Vin    | - 0.3 | + 6.5                           | V    |
| Power Dissipation    | PD     |       | 350<br>(T <sub>A</sub> ≤ +70°C) | mW   |
| Storage Temperature  | Tstg   | - 55  | + 125                           | °C   |

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

# RECOMMENDED OPERATING CONDITIONS

| Parameter               | Symbol | Value |      | Unit |
|-------------------------|--------|-------|------|------|
|                         |        | Min   | Max  | Unit |
| Power Supply Voltage    | Vcc    | 2.5   | 40   | V    |
| Operating Temperature   | ТА     | - 20  | + 75 | °C   |
| Output Current at pin 4 | IO4    | —     | 4.5  | mA   |
| Output Current at pin 6 | IO6    |       | 3.0  | mA   |

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

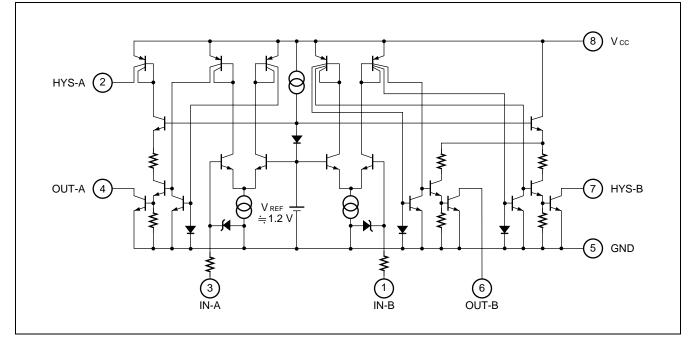
# ■ ELECTRICAL CHARACTERISTICS

(TA=+25°C, VCC=5 V)

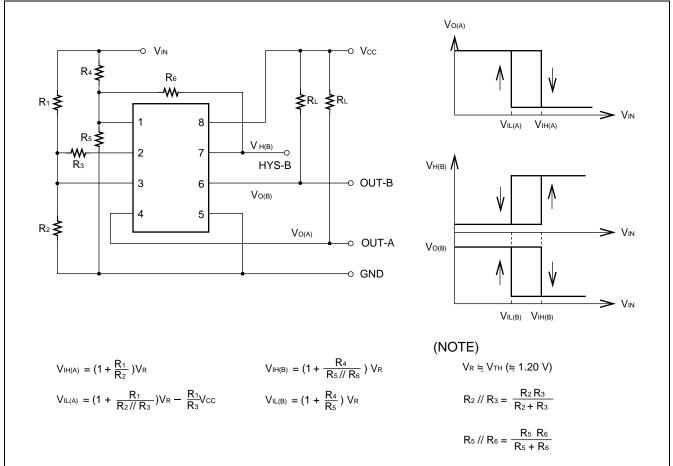
| Parameter   | Symbol Conditions | Value  |      |       |      |       |
|---|-------------------|--|------|-------|------|-------|
|   |                   | Conditions                                       | Min  | Тур   | Max  | Unit  |
| Power Supply Voltage  | ICCL              | VCC= 40 V, VIL= 1.0 V                            | -    | 250   | 400  | μΑ    |
|   | Іссн              | VCC= 40 V, VIH= 1.5 V                            | -    | 400   | 600  | μA    |
| Threshold Voltage   | Vтн               | Io = 2 mA, Vo= 1 V                               | 1.15 | 1.20  | 1.25 | V     |
| Deviation of Threshold<br>Voltage                             | $\Delta V$ TH1    | $2.5 \text{ V} \le \text{Vcc} \le 5.5 \text{ V}$ | -    | 3     | 12   | mV    |
|   | $\Delta$ Vth2     | $4.5 \text{ V} \le \text{Vcc} \le 40 \text{ V}$  | -    | 10    | 40   | mV    |
| Offset Voltage between<br>Outputs                             | Voosa             | IOA= 4.5 mA, VOA= 2 V,<br>IHA= 20 μA, VHA= 3 V   | -    | 2.0   | -    | mV    |
|   | Vossb             | IOB= 3 mA, VOB= 2 V,<br>IHB= 3 mA, VHB= 2 V      | -    | 2.0   | -    | mV    |
| Temperature Coefficient of<br>Threshold Voltage               | α                 | $-20^{\circ}C \le TA \le +70^{\circ}C$           | -    | ±0.05 | -    | mV/°C |
| Difference Voltage on<br>Threshold Voltage between<br>Channel | $\Delta$ Vthab    |  | -10  | -     | -10  | mV    |
| Input Current   | lı∟               | VIL= 1.0 V                                       | -    | 5     |      | nA    |
|   | Ін                | VIH= 1.5 V                                       | -    | 100   | 500  | nA    |
| Output Leakage Current  | Іон               | Vo= 40 V, VIL= 1.0 V                             | -    | -     | 1    | μΑ    |
| Hysteresis Output Leakage<br>Current                          | Ihla              | VCC= 40 V, VHA= 0 V,<br>VIL= 1.0 V               | -    | -     | 0.1  | μA    |
|   | Іннв              | VHB= 40 V, VIH= 1.5 V                            | -    | -     | 1    | μΑ    |
| Output Sink Current   | IOLA              | Vo= 1.0 V, VIH= 1.5 V                            | 6    | 12    | -    | mA    |
|   | IOLB              | Vo= 1.0 V, VIH= 1.5 V                            | 4    | 10    | -    | mA    |
| Hysteresis Current  | Інна              | VH= 0 V, VIH= 1.5 V                              | 40   | 80    | -    | μΑ    |
|   | Ihlb              | VH= 1.0 V,VIL= 1.0 V                             | 4    | 10    | -    | mA    |
| Output Saturation Voltage                                     | Vola              | IO= 4.5 mA, VIH= 1.5 V                           | -    | 120   | 400  | mV    |
|   | Volb              | IO= 3.0 mA, VIH= 1.5 V                           | -    | 120   | 400  | mV    |
| Hysteresis Saturation   | Vhha              | IH= 20 μA, VIH= 1.5 V                            | -    | 50    | 200  | mV    |
|   | Vhlb              | IH= 3.0 mA, VIL= 1.0 V                           | -    | 120   | 400  | mV    |
| Output Delay Time   | <b>t</b> PHL      | RL= 5 kΩ   | -    | 2     | -    | μs    |
|   | tPLH              | RL= 5 kΩ   | -    | 3     | -    | μs    |

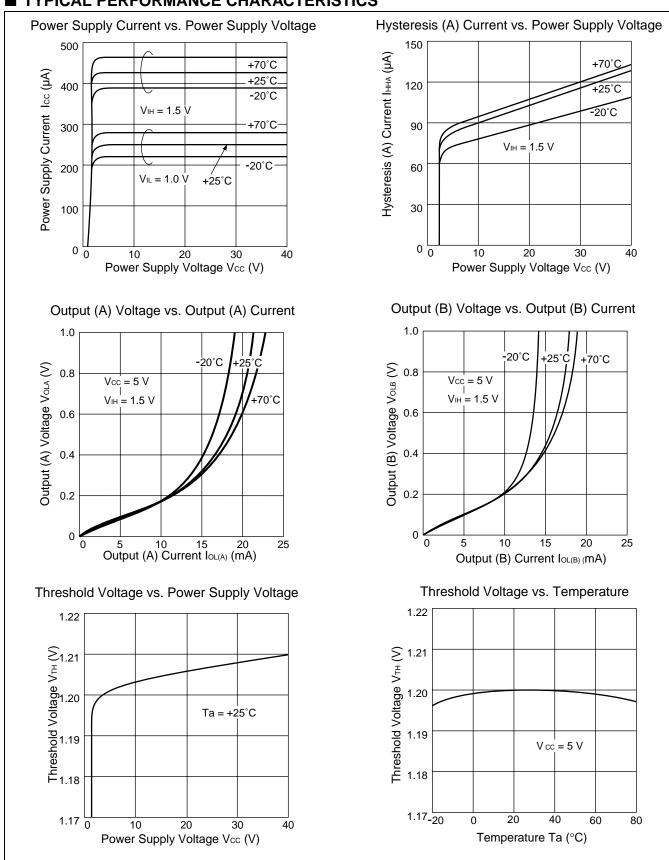
# **MB3761**

### EQUIVALENT CIRCUIT



### OPERATIONAL DEFINITIONS

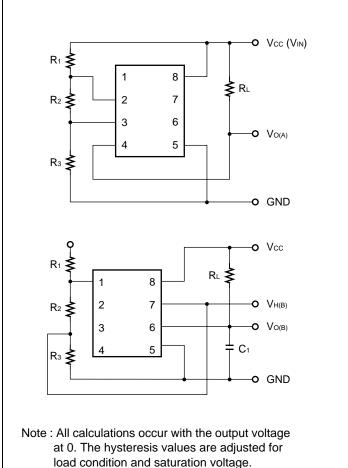


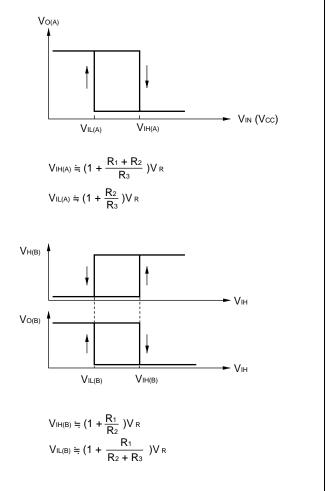


# ■ TYPICAL PERFORMANCE CHARACTERISTICS

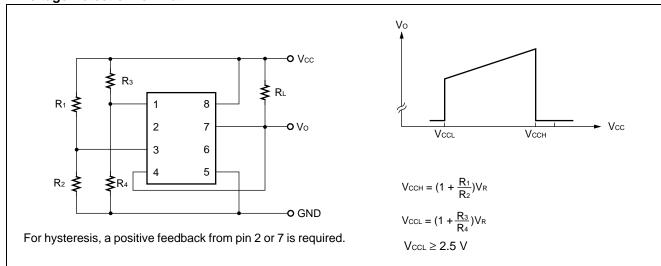
# ■ APPLICATION EXAMPLES

#### 1. Addition of Hysteresis

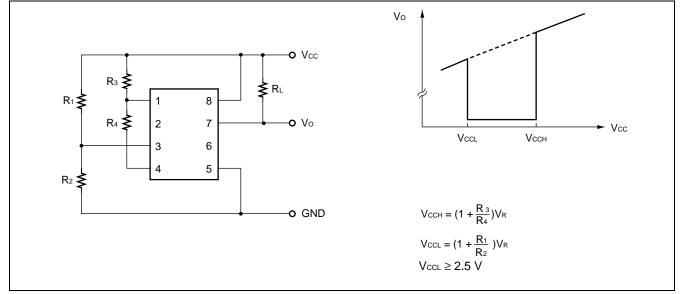




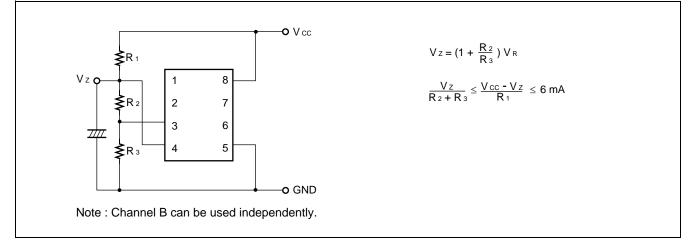
#### 2. Voltage Detection for Alarm



### 3. Voltage Detection for Alarm



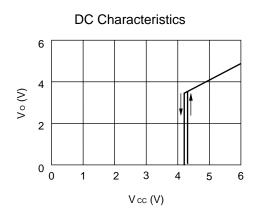
#### 4. Programmable Zener



# **MB3761**

#### 5. Recovery Reset Circuit $-\mathbf{o}$ V cc = 5 V R₁≸ $15 \ k\Omega$ **R** 2 3.3 kΩ **Š** E R₄ ≰ 330 kΩ 8 -**o** out 1 2 7 3 6 6.8 kΩ R ₃ ≰ R ₅ **\$** 6.8 kΩ 5 4 0.1 μF\_ C 1 --0 OUT -o GND

# ■ TYPICAL CHARACTERISTICS



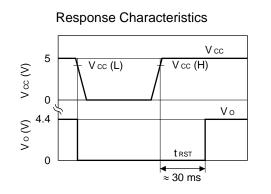
• Voltage Threshold Levels (VCCL and VCCH) and Hysteresis Width can be changed by the resistors (R1 through R4).

$$V_{CCL} = \frac{R_1 + R_2 + R_3}{R_3} V_{TH}$$
$$V_{CCH} = V_{CCL} + \frac{R_1 (R_2 + R_3)}{R_3 R_4} V_{TH}$$

 Power-On Reset Time is provided by the following approximate equation:

tRST = -C1 R4 • In 
$$\left\{1 - \frac{V_{TH}}{V_{CC}} \left(1 + \frac{R_1}{R_2 + R_3}\right)\right\}$$

- The recommended value of hFE of the external transistor is from 50 to 200.
- In the case of an instant power fail, the remaining charge in C1 effects tRST.
- If necessary, the reversed output is provided on HYS terminal



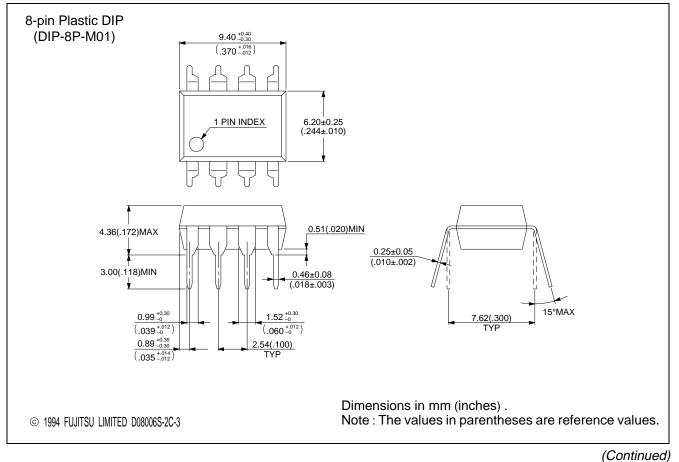
# NOTES ON USE

- Take account of common impedance when designing the earth line on a printed wiring board.
- Take measures against static electricity.
  - For semiconductors, use antistatic or conductive containers.
  - When storing or carrying a printed circuit board after chip mounting, put it in a conductive bag or container.
  - The work table, tools and measuring instruments must be grounded.
  - The worker must put on a grounding device containing 250 k $\Omega$  to 1 M $\Omega$  resistors in series.
- Do not apply a negative voltage
  - Applying a negative voltage of –0.3 V or less to an LSI may generate a parasitic transistor, resulting in malfunction.

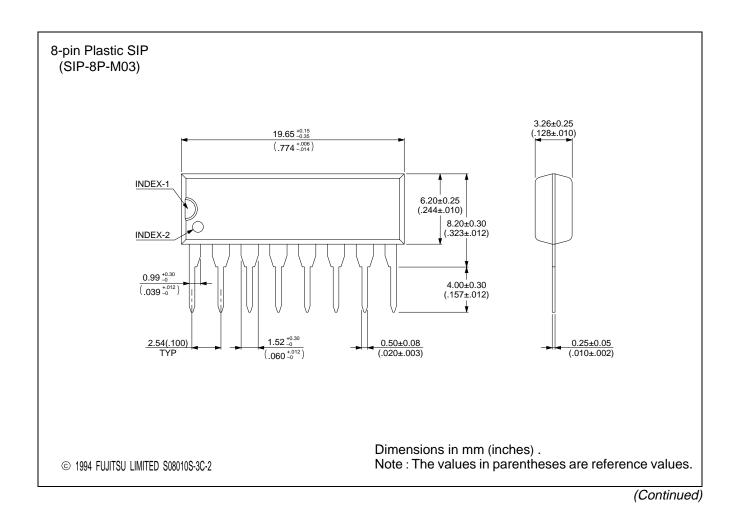
| Part number | Package                           | Remarks |
|-------------|-----------------------------------|---------|
| MB3761M     | 8-pin Plastic DIP<br>(DIP-8P-M01) |         |
| MB3761PS    | 8-pin Plastic SIP<br>(SIP-8P-M03) |         |
| MB3761PF    | 8-pin Plastic SOP<br>(FPT-8P-M01) |         |

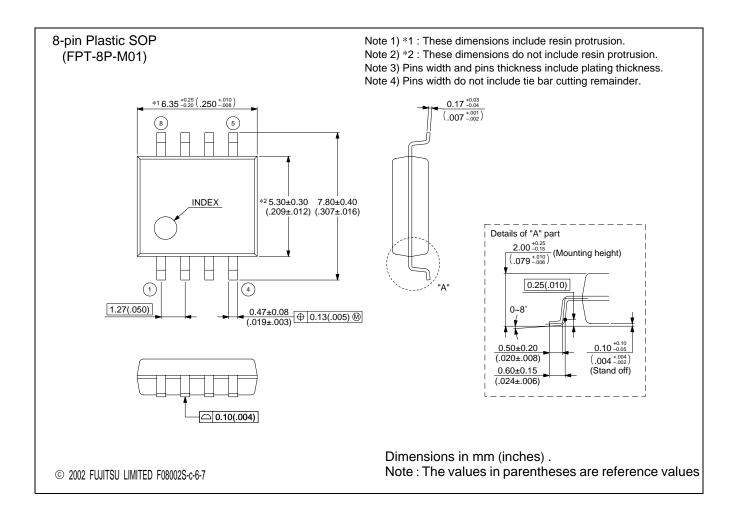
### ORDERING INFORMATION

# ■ PACKAGE DIMENSION



# **MB3761**





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